

## ABSTRACT OF THE DISCLOSURE

- 5           Processes for precursors for silicon dielectric depositions of silicon nitride, silicon oxide and silicon oxynitride on a substrate using a hydrazinosilane of the formula:



- 10   where each  $R^1$  is independently selected from alkyl groups of  $C_1$  to  $C_6$ ; each  $R^2$  is independently selected from the group consisting of hydrogen, alkyl, vinyl, allyl, and phenyl; and  $n = 1-4$ . Some of the hydrazinosilanes are novel precursors.